# 1 Flash-Based SSDs

## Vocabularies

## 1. Flash Solid-State Storage

• Is a type of non-volatile computer storage that stores and retrieves digital information using only electronic circuits, without any involvement of moving mechanical parts

#### 2. NAND-Based Flash

• Is an electronic non-volatile computer memory storage medium using NAND-gate that can be electrically erased and reprogrammed.

## 3. Flash Page

• Is the smallest unit that can be programmed into flash

#### 4. Flash Block

• Is a group of pages and the smallest unit that can be erased.



## 5. Wear Out

- Is similar to going past expiration date
- Means it has exceeded their endurance rating

## 6. Single-Level Cell

• Is a type of cell in solid-state storage that stores one bit of data per transister (0 or 1)

#### 7. Multi-Level Cell

• Is a type of cell in solid-state storage that stores two bits of data (i.e 00, 01, 10, 11) per cell using two different levels of charge

## 8. Triple-Level Cell

• Is a type of cell in solid-state storage that stores three bits of data per cell (i.e 000, 001, 010, 011, 100, 101, 110, 111)

## 9. Bank / Plane

• Is a group of large number of cells

#### 10. Head Crash

• Is a condition where the drive head makes contact with the recording surface



#### 11. Disturbance

- Is also known as read disturbance or program disturbance
- Is a condition where accessing a bit in a page causes some bits to get flipped in neighboring pages

#### 12. Flash Transition Layer

• Is an intermediate system made up software and hardware that manages SSD operations



## 13. Wear Leveling

• Is a technique for prolonging the service life of some kinds of erasable computer storage media, such as flash memory, which is used in solid-state drives (SSDs)

## 14. Direct Mapped

• Is a simplest organization of an **Flash Transition Layer** that maps read of logical page N directly to read of playsical page N.

#### 15. Logging

• Is a concept in **log-structured file system** that buffer all writes (data + metadata) using an in-memory segment; once the segment is full, write the segment to a log

#### 16. Mapping Table

• Is a table that stores the physical address of each logical block in the system

#### 17. Logical Block Address

• Is a common scheme used for specifying the location of blocks of data stored on computer storage devices, generally in secondary storage system



## 18. In-Memory Mapping Table

• Is a table inside the memory of the secondary storage device (is persistent in some form) that stores the physical address of each logical block in the system

## 19. Garbage Block

- Is also called **Dead Block**
- Is old version of block in secondary storage, such as solid state drive

## 20. Garbage Collection

• Is the process of finding garbage blocks and reclaiming them for future use

#### 21. Cache Flush

• Is the process of clearing out sections of memory to ensure writes have actually been persisted in solid state drive

## 22. **Trim**

• Is an operation that takes an address (and possibly a length) and informs the device that the block(s) specified by the address (and length) have been deleted



## 23. Overprovision

• Is an extra amount of flash space used to reduce the cost of **garbage collection**, increase the logitivity of flash drive, and prevents the device from slowing down



## 24. Page-Level FTL

- Is an intermediate system made of software and hardware that manages SSD operations at page-level.
  - It does not write a full block
  - Only writes the necessary page(s) of data along with the FTL metadata that must be written to track of the new position of the data

## 25. Hybrid Mapping

• Is a mapping technique used in **Flash Transition Layer** that utilizes both block-based mapping and page-based mapping to enable flexible writing but also reduce mapping costs

#### 26. Log Blocks

 Are blocks in solid state storage where contents are erased and all writes are directed

## 27. Switch Merge

• This will be revisited when reading related section

#### 28. Partial Merge

• This will be revisited when reading related section

## 29. Full Merge

• This will be revisited when reading related section

#### 1.1 Flash-Based SSDs

- Has two interesting problems to overcome
  - 1. To write a small chunk (called **flash page**), a bigger chunk (**flash block**) must be erased first
  - 2. Writing too often would cause a page to wear out

# 1.2 Storing a Single Bit

- Single-level cell  $\rightarrow$  1 bit per cell
- Multi-level cell  $\rightarrow$  2 bits per cell
- Triple-level cell  $\rightarrow$  3 bits per cell
- Single-level cell has higher performance and are more expensive
  - More 촘촘하다
- How SLC, MLC, TLC works  $\rightarrow$  Physics!!

# 1.3 From Bits to Banks / Planes

Question Is conent in a flash chip a cell? How many bits can be stored per content?

Question I should ask clarification from professor about why Samsung and other tech giants are producing higher level cells if SLC is better in performance

- In each plane/bank, there are large number of blocks
- In each block, there are a large number of pages



# 1.4 Basic Flash Operations

- Read (a page):
  - Is fast (  $10 \mu s$ )
  - Can access any location uniformly
    - \* flash-based SSD is a random access device
- Erase (a block):
  - Is most expensive
  - block must be erased before erasing a page



## • Program (a page):

- Is used to change some of the 1's within a page to 0's and vice versa
- Is less expensive then erasing a block
- Is more costly than reading a page
- Before overwriting any page within a block, we must first move any data we care about to another location
  - \* Frequent repeatitions of program/erase cycle cause flash chips to wear out
- Page starts in INVALID state
- Erasing block results in pages with ERASED state
  - resets contents in page
  - makes contents re-programmable
- Programming a page results in VALID state
  - Contents are set and can be read
  - Only way to change it's content is to erase the entire block

```
iiii
                             Initial: pages in block are invalid (i)
Erase()
                    EEEE
                             State of pages in block set to erased (E)
Program(0)
                            Program page 0; state set to valid (V)
                    VEEE
Program(0)
                    error
                             Cannot re-program page after programming
Program(1)
                    VVEE
                            Program page 1
                    EEEE
                             Contents erased; all pages programmable
```

## 1.5 Flash Performance and Reliability

#### • Performance

		Read	Program	Erase	Slower
	Device	(μs)	(μs)	(μs)	as more bits
Single-layer cell ———	→ SLC	25	200-300	1500-2000	packed per
Multi-layer cell ———	MLC	50	600-900	~3000	packed per
Triple-layer cell ———	→ TLC	~75	~900-1350	~4500	cell

## • Reliability Concerns

## - Wear Out

- \* Accures a bit of extra charge when flash block is erased and programmed
- \* Over time, 0 and 1 become difficult to distinguish
- \* Becomes unusable at the point where it becomes impossible to distinguish

#### - Disturbance

- \* Access a page within a flash may cause some bits to get flipped in neighboring pages
- \* Disturbance while programming  $\rightarrow$  Program Disturbance
- \* Disturbance while reading  $\rightarrow$  Read Disturbance

### 1.6 From Raw Flash to Flash-Based SSDs

- Addresses the question "How to turn a basic set of flash chips into something that looks like a typical storage device"
- Hardware Requirements
  - Flash chips
  - Some volatile memory for caching (e.g. SRAM)
  - Control logic to orchestrate device operation

#### • Other Requirements

#### Flash Transition Layer

- \* Is made up of both hardware and software
- \* Takes read and write requests on logical blocks
- \* Turns contents in logical blocks into low-level read, erase, and program commands on the underlying  $physical\ page$  and  $physical\ block$
- \* FTL should accomplish this task with the goal of excellent performance and high reliability

#### 1. Performance

· Running in **parallel** - using multiple chips internally boosts performance

Is similar to using multiple disk arm on HDD

- 2. Reliability
  - Wear Leveling Spreading writes across the blooks of flash as evenly as possible
    - Address wear out
    - Slows the buildup of charge
  - · Writing page in order from low page to high page
    - Minimize disturbance

# 1.7 FTL Organization: A Bad Approach

- Direct Mapped
  - How it works
    - \* Read
      - · Directly translates the read of logical page N to a read of physical page N
    - \* Write
      - · Read in the entire block page N is contained within
      - · Erase the block
      - · Program the old page as well as the new one
  - Creates write amplification (performance problem)
    - \* Write is proportional to number of pages in a block
      - · Reading entire block is costly, Erasing it is costly, and programming it is costly
    - \* Results in terrible write performance
    - \* Is slower than typical hard drives
  - Doesn't follow wear leveling (reliability problem)
    - \* User file data is repeatedly over written
    - \* Results in wear out and potentially loses data

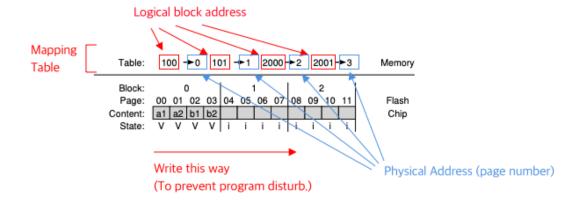
# 1.8 A Log Structured FTL

- Works similarly as log structured file system
- Is useful in storage device and file system
- How it works

- Keeps a **logical block** N
  - \* The device appends the write to the next free spot in the currently-beingwritten to block
- Keeps a mapping table
- Translate contents from logical address to physical address
  - \* Is done when logical block is full

## Example

- Write logical address (100) with content a1
- Write logical address (101) with content a2
- Write logical address (2000) with content b1
- Write logical address (2001) with content b2



- Advantages
  - Improves performance
  - Greatly enhances reliability
- 1.9 Garbage Collection
- 1.10 Mapping Table Size
- 1.11 Hybrid Mapping
- 1.12 Wear Leveling
- 1.13 SSD Performance And Cost